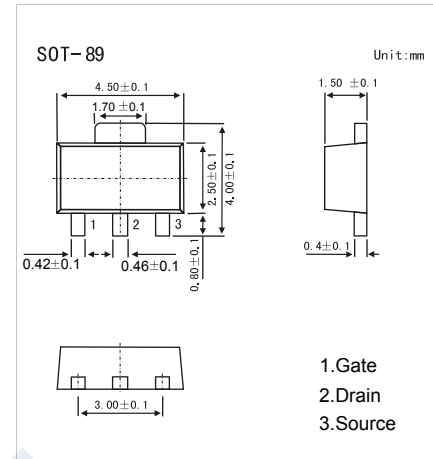
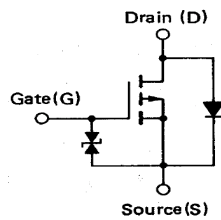


P-Channel MOSFET

2SJ207

■ Features

- $V_{DS} (V) = -16V$
- $I_D = -1 A (V_{GS} = -10V)$
- $R_{DS(ON)} < 1.5 \Omega (V_{GS} = -4V)$
- $R_{DS(ON)} < 4 \Omega (V_{GS} = -2.5V)$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-16	V
Gate-Source Voltage	V_{GS}	± 16	
Continuous Drain Current	I_D	-1	A
Pulsed Drain Current (Note.1)	I_{DM}	-2	
Power Dissipation	P_D	2	W
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $PW \leq 10$ ms, duty cycle $\leq 50\%$

■ Electrical Characteristics $T_a = 25^\circ C$

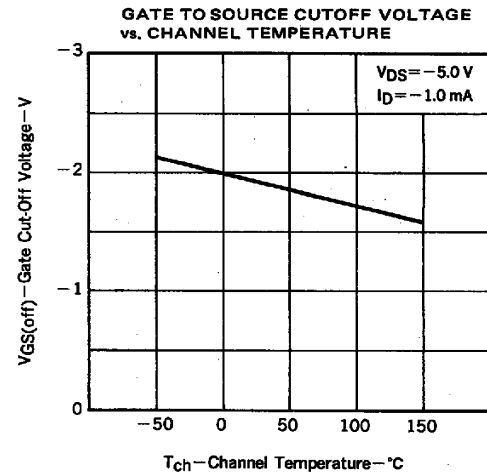
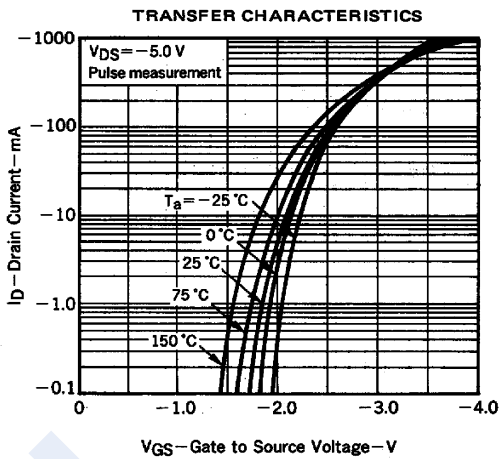
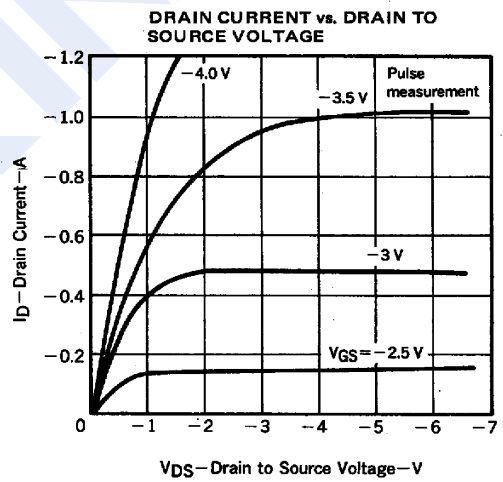
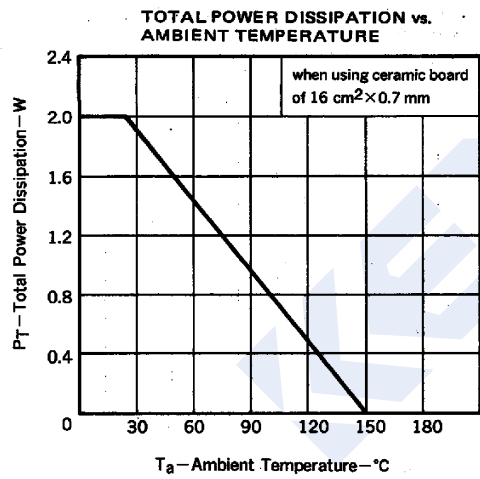
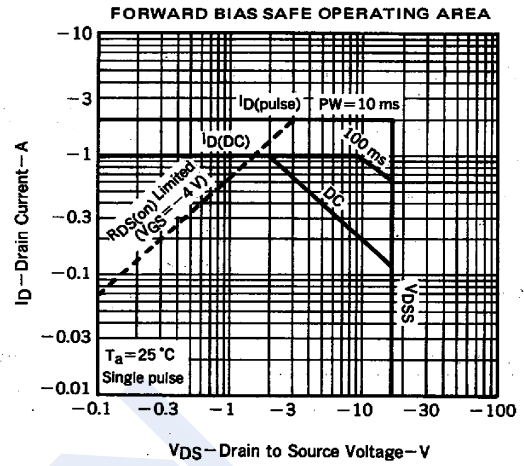
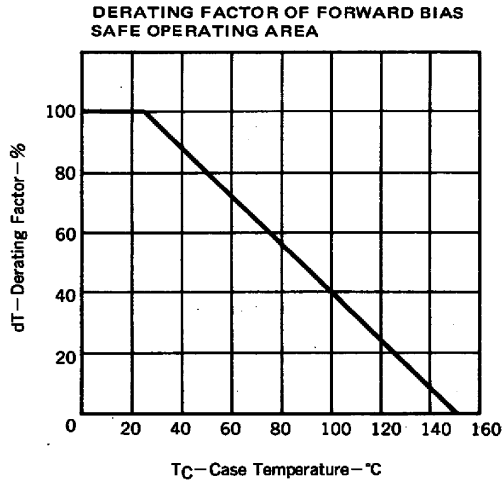
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = -250 \mu A, V_{GS} = 0V$	-16			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16V, V_{GS} = 0V$			-1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 16V$			± 5	μA
Gate to Source Cutoff Voltage	$V_{GS(off)}$	$V_{GS} = -5V, I_D = -1mA$	-1.4		-2.4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4V, I_D = -0.5A$			1.5	Ω
		$V_{GS} = -2.5V, I_D = -30mA$			4	
Forward Transconductance	g_{FS}	$V_{DS} = -3V, I_D = -0.5A$	0.4	0.7		S
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = -3V, f = 1MHz$		180		pF
Output Capacitance	C_{oss}			160		
Reverse Transfer Capacitance	C_{rss}			50		
Turn-On DelayTime	$t_{d(on)}$	$V_{GS(on)} = -3V, I_D = -0.1A, R_L = 30 \Omega, R_G = 10 \Omega, V_{DD} = -3V,$		180		ns
Turn-On Rise Time	t_r			500		
Turn-Off DelayTime	$t_{d(off)}$			130		
Turn-Off Fall Time	t_f			240		

■ Marking

Marking	PE
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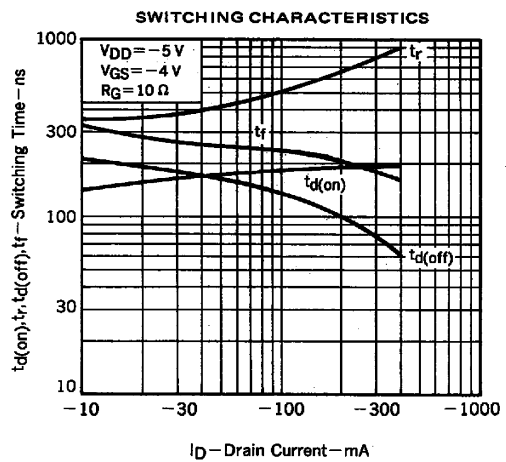
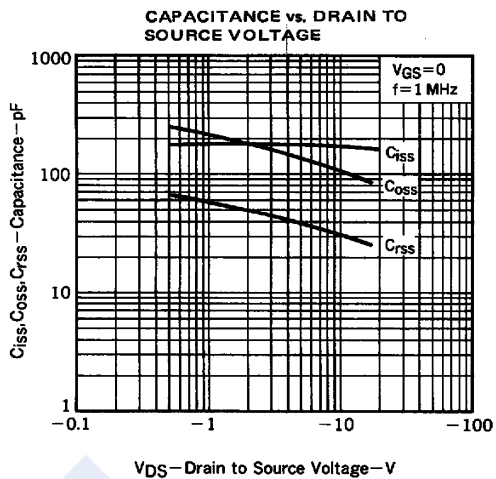
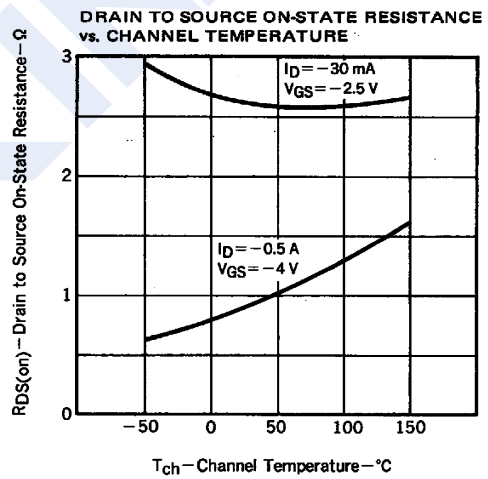
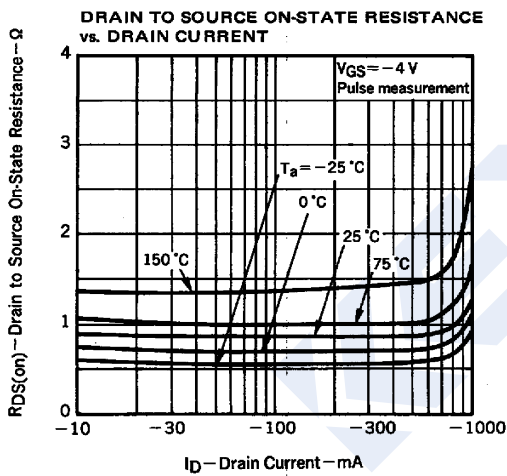
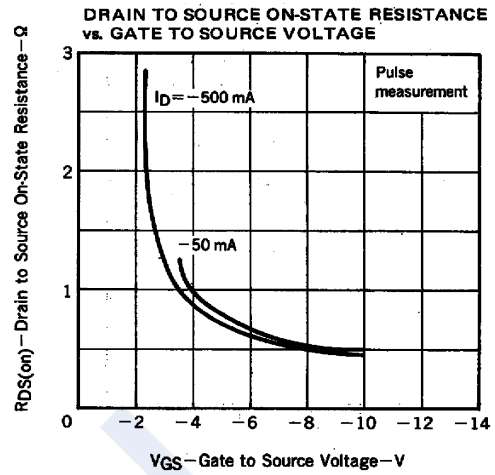
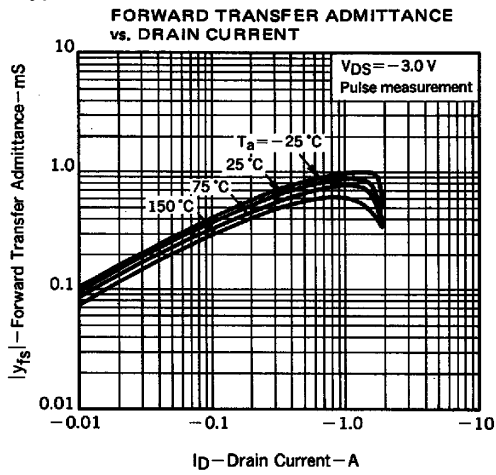
P-Channel MOSFET 2SJ207

■ Typical Characteristics



P-Channel MOSFET 2SJ207

■ Typical Characteristics



P-Channel MOSFET

2SJ207

■ Typical Characteristics

